


REMARKS

In response to the election requirement in the Office Action of February 19, 2003, Applicant hereby elects without traverse the Group IV claims - that is, claims 47, 51, 53, 55, 59, and 63.

Claims 47, 66 and 67 have been amended to correct minor matters of form. Furthermore, new independent claim 78 and dependent claims 79 and 80 are added herewith. Independent claim 78 is generic to at least independent claims 1, 10, 46, 47, 48, 66 and 67 and the claims dependent therefrom.

Examination on the merits is requested.

Respectfully submitted,



Eric J. Robinson
Reg. No. 38,285
Robinson Intellectual Property Law Office, P.C.
PMB 955
21010 Southbank Street
Potomac Falls, Virginia 20165
(571) 434-6789

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Please amend claims 47, 66, and 67 as follows:

47. (Amended) A method of manufacturing a semiconductor device comprising:

forming a first semiconductor film having an amorphous structure over a substrate;

providing the first semiconductor film with a material for promoting crystallization;

heating the first semiconductor film for crystallizing;

irradiating the first semiconductor film with a laser light for improving crystallinity;

forming a barrier layer over the first semiconductor film having crystalline structure;

forming a second semiconductor film over the barrier layer [, the second semiconductor film comprising an inert gas element];

adding an inert gas element to an upper layer of the second semiconductor film;

gettering the material for promoting crystallization into the upper layer of the second semiconductor film.

66. (Amended) A method of manufacturing a semiconductor device comprising:

providing a crystalline semiconductor film comprising silicon over a substrate, said crystalline semiconductor film containing metallic element;

forming a barrier layer over the crystalline semiconductor film;

forming a second semiconductor film over the barrier layer;

forming a third semiconductor film comprising an inert gas element over the second semiconductor film;

gettering the metallic element into the third semiconductor film to remove or reduce the amount of the metallic element within the [first semiconductor film having a crystalline structure] crystalline semiconductor film; and

removing the second semiconductor film and the third semiconductor film.

67. (Amended) A method of manufacturing a semiconductor device comprising:

providing a crystalline semiconductor film comprising silicon over a substrate, said crystalline semiconductor film containing metallic element;

forming a barrier layer over the crystalline semiconductor film;

forming a second semiconductor film over the barrier layer;

adding an inert gas element to an upper layer of the second semiconductor film;

gettering the metallic element into the upper layer of the second semiconductor film to remove or reduce the amount of the metallic element within the crystalline semiconductor film [having a crystalline structure]; and

removing the second semiconductor film.